CY62157H30-45BVXA
Automotive

8-Mbit (512K Words × 16-Bit) Static RAM with Error-Correcting Code (ECC)

Features

- AEC-Q100 Qualified
- Ultra-low standby power
  - Typical standby current: 5.5 µA
  - Maximum standby current: 16 µA
- High speed: 45 ns
- Embedded error-correcting code (ECC) for single-bit error correction
- Temperature Ranges:
  - Automotive-A: –40 °C to +85 °C
- Operating voltage range: 2.2 V to 3.6 V
- 1.0 V data retention
- TTL-compatible inputs and outputs
- Available in Pb-free 48-ball VFBGA package

Functional Description

CY62157H30-45BVXA is high-performance CMOS low-power (MoBL) SRAM device with embedded ECC. This device is offered in dual chip-enable.

Devices with dual chip-enable are accessed by asserting both chip-enable inputs – $\overline{CE}_1$ as LOW and CE_2 as HIGH.

Data writes are performed by asserting the Write Enable input ($\overline{WE}$) LOW, and providing the data and address on device data (I/O_0 through I/O_{15}) and address (A_0 through A_{19}) pins respectively. The Byte High/Low Enable ($\overline{BHE}$, $\overline{BLE}$) inputs control byte writes, and write data on the corresponding I/O lines to the memory location specified. $\overline{BHE}$ controls I/O_8 through I/O_{15}; $\overline{BLE}$ controls I/O_0 through I/O_7.

Data reads are performed by asserting the Output Enable ($\overline{OE}$) input and providing the required address on the address lines. Read data is accessible on I/O lines (I/O_0 through I/O_{15}). Byte accesses can be performed by asserting the required byte enable signal ($\overline{BHE}$, $\overline{BLE}$) to read either the upper byte or the lower byte of data from the specified address location.

All I/Os (I/O_0 through I/O_{15}) are placed in a HI-Z state when the device is deselected ($\overline{CE}_1$ HIGH / CE_2 LOW for dual chip-enable device), or control signals are de-asserted ($\overline{OE}$, $\overline{BLE}$, and $\overline{BHE}$).

These devices also have a unique “Byte Power down” feature where if both the Byte Enables ($\overline{BHE}$ and $\overline{BLE}$) are disabled, the devices seamlessly switches to standby mode irrespective of the state of the chip enable(s), thereby saving power.

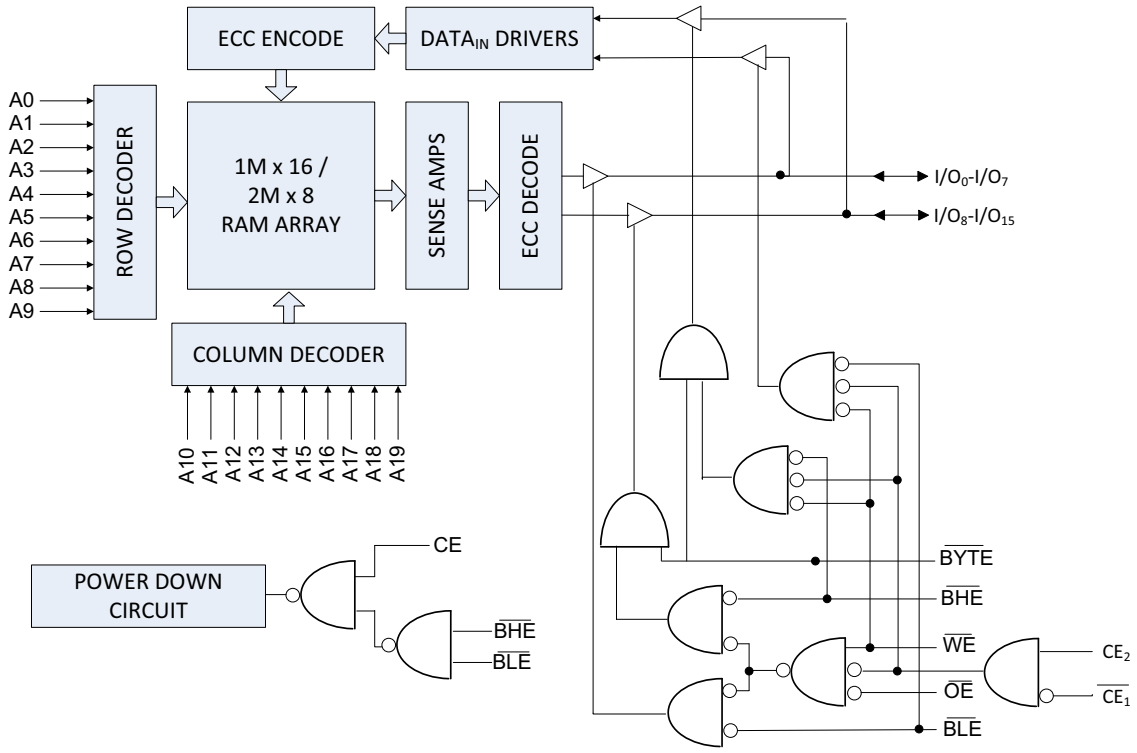
The logic block diagram is on page 2. Refer to Pin Configurations on page 4 and the associated footnotes for details.

Product Portfolio

Product	Range	V_{CC} Range (V)	Speed (ns)	Power Dissipation			
				Operating I_{CC}, (mA), f = f_{max}		Standby, I_{SB2} (µA)	
				Typ [2]	Max	Typ [2]	Max
CY62157H30-45BVXA	Automotive-A	2.2 V–3.6 V	45	29.0	36.0	5.5	16.0

Note
1. This device does not support automatic write-back on error detection.
2. Indicates the value for the center of Distribution at 3.0 V, 25 °C and not 100% tested.

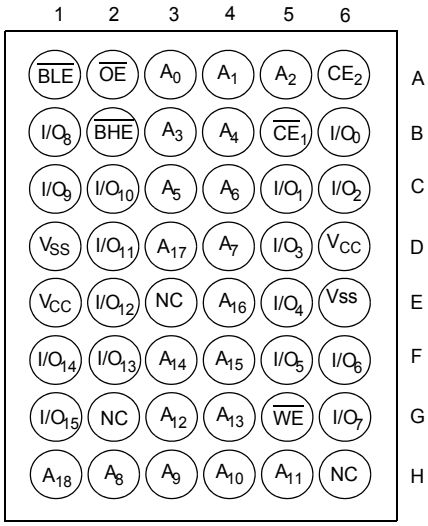
Logic Block Diagram – CY62157H30-45BVXA



Contents

Pin Configurations

Figure 1. 48-ball VFBGA pinout [3]
CY62157H30-45BVXA



Note
3. NC pins are not connected internally to the die and are typically used for address expansion to a higher-density device. Refer to the respective datasheets for pin configuration.

Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. User guidelines are not tested.

Storage temperature ..... –65 °C to + 150 °C

Ambient temperature with power applied ..... –55 °C to + 125 °C

Supply voltage to ground potential [4] ..... –0.5 V to V_{CC} + 0.5 V

DC voltage applied to outputs in High-Z state [4] ..... –0.5 V to V_{CC} + 0.5 V

DC input voltage [4] ..... –0.5 V to V_{CC} + 0.5 V

Output current into outputs (LOW) ..... 20 mA

Static discharge voltage (MIL-STD-883, Method 3015) ..... >2001 V

Latch-up current ..... >140 mA

Operating Range

Grade	Ambient Temperature	V_{CC}
Automotive-A	–40 °C to +85 °C	2.2 V to 3.6 V

DC Electrical Characteristics

Over the Operating Range

Parameter	Description		Test Conditions		45 ns (Automotive-A)			Unit
					Min	Typ [5]	Max	
V_{OH}	Output HIGH voltage	2.2 V to 2.7 V	V_{CC} = Min, I_{OH} = –0.1 mA		2.0	–	–	V
		2.7 V to 3.6 V	V_{CC} = Min, I_{OH} = –1.0 mA		2.4	–	–	
V_{OL}	Output LOW voltage	2.2 V to 2.7 V	V_{CC} = Min, I_{OL} = 0.1 mA		–	–	0.4	V
		2.7 V to 3.6 V	V_{CC} = Min, I_{OL} = 2.1 mA		–	–	0.4	
V_{IH}	Input HIGH voltage[4]	2.2 V to 2.7 V	–		2.0	–	V_{CC} + 0.3	V
		2.7 V to 3.6 V	–		2.0	–	V_{CC} + 0.3	
V_{IL}	Input LOW voltage[4]	2.2 V to 2.7 V	–		–0.3	–	0.6	V
		2.7 V to 3.6 V	–		–0.3	–	0.8	
I_{IX}	Input leakage current		GND ≤ V_{IN} ≤ V_{CC}		–1.0	–	+1.0	µA
I_{OZ}	Output leakage current		GND ≤ V_{OUT} ≤ V_{CC}, Output disabled		–1.0	–	+1.0	µA
I_{CC}	V_{CC} operating supply current		V_{CC} = Max, I_{OUT} = 0 mA, CMOS levels	f = f_{MAX}	–	29.0	36.0	mA
				f = 1 MHz	–	7.0	9.0	mA
I_{SB1}[6]	Automatic power down current – CMOS inputs; V_{CC} = 2.2 to 3.6 V		$\overline{CE_1}$ ≥ V_{CC} – 0.2 V or CE_2 ≤ 0.2 V or ($\overline{BHE}$ and $\overline{BLE}$) ≥ V_{CC} – 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V, V_{IN} ≤ 0.2 V, f = f_{max} (address and data only), f = 0 ($\overline{OE}$, and $\overline{WE}$), V_{CC} = $V_{CC(max)}$		–	5.5	16.0	µA
I_{SB2}[6]	Automatic power down current – CMOS inputs; V_{CC} = 2.2 to 3.6 V		$\overline{CE_1}$ ≥ V_{CC} – 0.2V or CE_2 ≤ 0.2 V or ($\overline{BHE}$ and $\overline{BLE}$) ≥ V_{CC} – 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V or V_{IN} ≤ 0.2 V, f = 0, V_{CC} = $V_{CC(max)}$		–	5.5	16.0	µA

Notes
4. $V_{IL(min)}$ = –2.0 V and $V_{IH(max)}$ = V_{CC} + 2 V for pulse durations of less than 2 ns.
5. Indicates the value for the center of Distribution at 3.0 V, 25 °C and not 100% tested.
6. Chip enables ($\overline{CE_1}$ and CE_2) and $\overline{BHE}$, $\overline{BLE}$ must be tied to CMOS levels to meet the I_{SB1}/I_{SB2}/I_{CCDR} spec. Other inputs can be left floating.

Capacitance

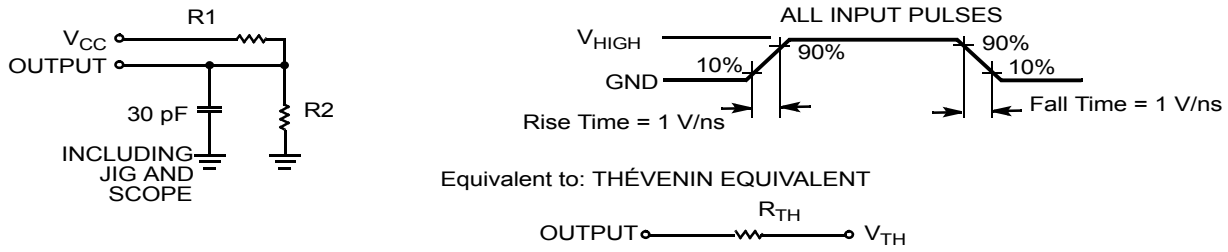
Parameter [7]	Description	Test Conditions	Max	Unit
C_{IN}	Input capacitance	T_A = 25 °C, f = 1 MHz, V_{CC} = $V_{CC(typ)}$	10	pF
C_{OUT}	Output capacitance		10	pF

Thermal Resistance

Parameter [7]	Description	Test Conditions	48-ball VFBGA	Unit
Θ_{JA}	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	31.50	°C/W
Θ_{JC}	Thermal resistance (junction to case)		15.75	°C/W

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms



Parameters	3.0 V	Unit
R1	317	Ω
R2	351	Ω
V_{HIGH}	3.0	V

Note
7. Tested initially and after any design or process changes that may affect these parameters.

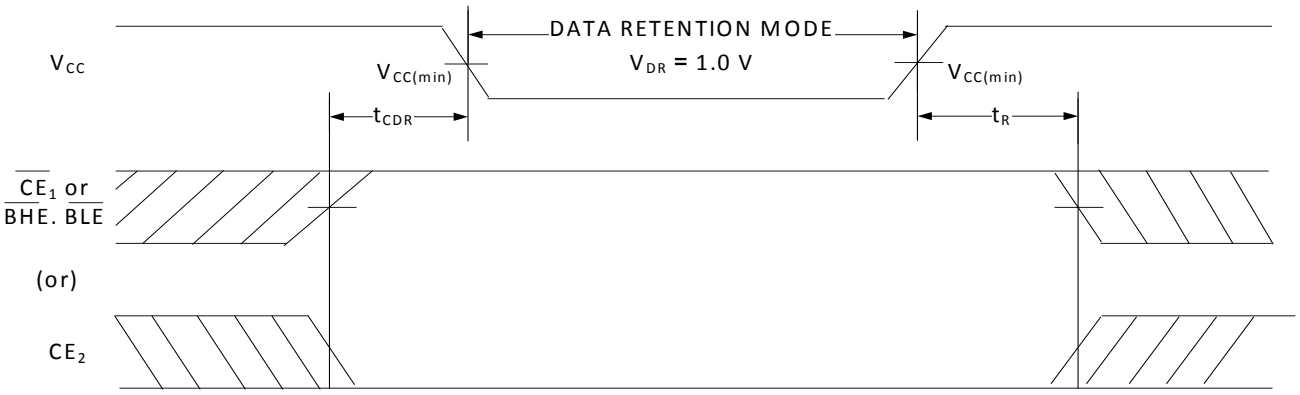
Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	45 ns (Automotive -A)			Unit
			Min	Typ [8]	Max	
V_{DR}	V_{CC} for data retention		1	–	–	V
I_{CCDR}[9]	Data-retention current	2.2 V < V_{CC} ≤ 3.6 V $\overline{CE_1}$ ≥ V_{CC} – 0.2 V or CE_2 ≤ 0.2 V or ($\overline{BHE}$ and $\overline{BLE}$) ≥ V_{CC} – 0.2 V, V_{IN} ≥ V_{CC} – 0.2 V or V_{IN} ≤ 0.2 V	–	5.5	16.0	µA
t_{CDR}[10]	Chip deselect to data-retention time		0	–	–	–
t_R[11]	Operation-recovery time		45	–	–	ns

Data Retention Waveform

Figure 3. Data-Retention Waveform [12]



Notes
8. Indicates the value for the center of distribution at 3.0 V, 25°C and not 100% tested.
9. Chip enables ($\overline{CE_1}$ and CE_2) must be tied to CMOS levels to meet the $I_{SB1}/I_{SB2}/I_{CCDR}$ spec. Other inputs can be left floating.
10. Tested initially and after any design or process changes that may affect these parameters.
11. Full device operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min)}$ ≥ 100 µs or stable at $V_{CC(min)}$ ≥ 100 µs.
12. $\overline{BHE}$.$\overline{BLE}$ is the AND of both $\overline{BHE}$ and $\overline{BLE}$. Deselect the chip by either disabling the chip enable signals or by disabling both $\overline{BHE}$ and $\overline{BLE}$.

Switching Characteristics

Parameter [13]	Description	45 ns (Automotive-A)		Unit
		Min	Max	
Read Cycle				
t_{RC}	Read cycle time	45	–	ns
t_{AA}	Address to data valid	–	45	ns
t_{OHA}	Data hold from address change	10	–	ns
t_{ACE}	$\overline{CE}_1$ LOW and CE_2 HIGH to data valid / $\overline{CE}$ LOW	–	45	ns
t_{DOE}	$\overline{OE}$ LOW to data valid / $\overline{OE}$ LOW	–	22	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z [14]	5	–	ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z [14, 15]	–	18	ns
t_{LZCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to Low Z [14]	10	–	ns
t_{HZCE}	$\overline{CE}_1$ HIGH and CE_2 LOW to High Z [14, 15]	–	18	ns
t_{PU}	$\overline{CE}_1$ LOW and CE_2 HIGH to power-up	0	–	ns
t_{PD}	$\overline{CE}_1$ HIGH and CE_2 LOW to power-down	–	45	ns
t_{DBE}	BLE / BHE LOW to data valid	–	45	ns
t_{LZBE}	$\overline{BLE}$ / $\overline{BHE}$ LOW to Low Z [14]	5	–	ns
t_{HZBE}	$\overline{BLE}$ / $\overline{BHE}$ HIGH to High Z [14, 15]	–	18	ns
Write Cycle [16 ,17]				
t_{WC}	Write cycle time	45	–	ns
t_{SCE}	$\overline{CE}_1$ LOW and CE_2 HIGH to write end	35	–	ns
t_{AW}	Address setup to write end	35	–	ns
t_{HA}	Address hold from write end	0	–	ns
t_{SA}	Address setup to write start	0	–	ns
t_{PWE}	$\overline{WE}$ pulse width	35	–	ns
t_{BW}	$\overline{BLE}$ / $\overline{BHE}$ LOW to write end	35	–	ns
t_{SD}	Data setup to write end	25	–	ns
t_{HD}	Data hold from write end	0	–	ns
t_{HZWE}	$\overline{WE}$ LOW to High Z [14, 15]	–	18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z [14]	10	–	ns

Notes

13. Test conditions assume signal transition time (rise/fall) of 3 ns or less, timing reference levels of 1.5 V (for $V_{CC} \geq 3$ V) and $V_{CC}/2$ (for $V_{CC} < 3$ V), and input pulse levels of 0 to 3 V (for $V_{CC} \geq 3$ V) and 0 to V_{CC} (for $V_{CC} < 3$ V). Test conditions for the read cycle use output loading shown in AC Test Loads and Waveforms section, unless specified otherwise.
14. At any temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZBE} is less than t_{LZBE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any device.
15. t_{HZOE}, t_{HZCE}, t_{HZBE}, and t_{HZWE} transitions are measured when the outputs enter a high impedance state.
16. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE}_1$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write. Any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write
17. The minimum write cycle pulse width for the Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW) should be equal to the sum of t_{SD} and t_{HZWE}.

Switching Waveforms

Figure 4. Read Cycle No. 1 of CY62157H30-45BVXA (Address Transition Controlled) [18, 19]

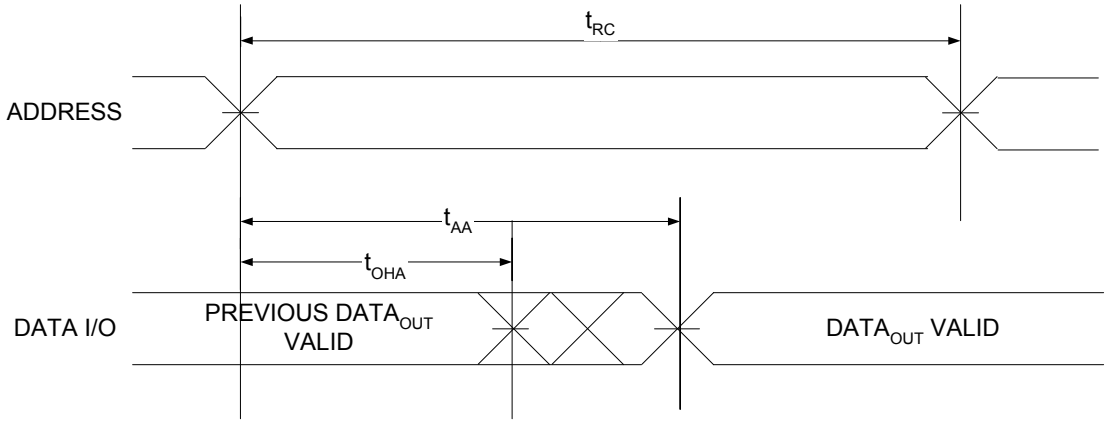
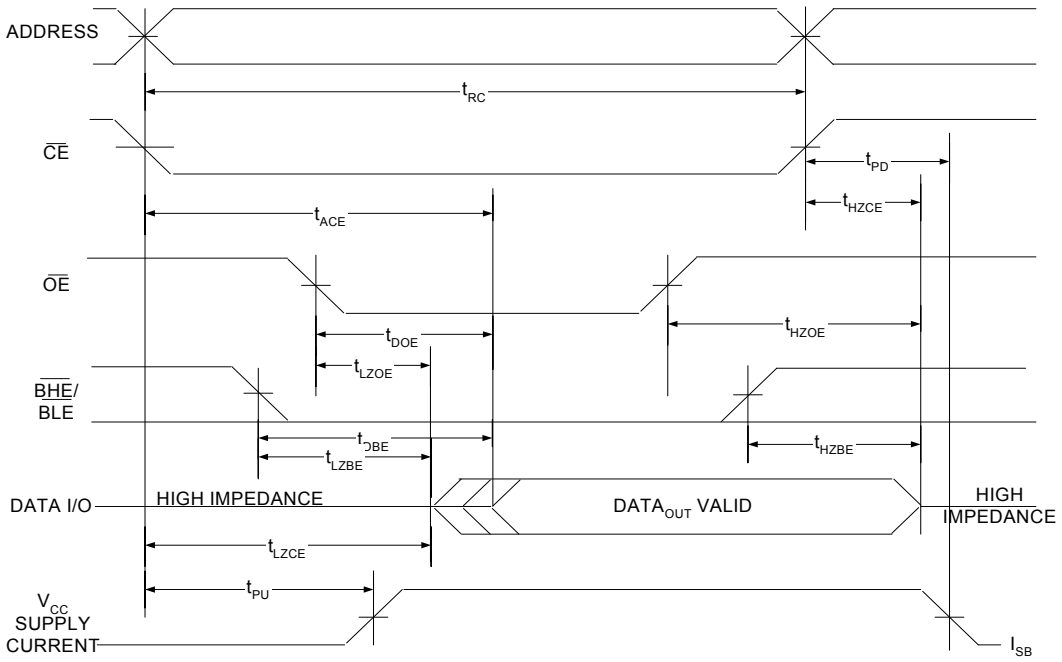


Figure 5. Read Cycle No. 2 ($\overline{OE}$ Controlled) [19, 20, 21]

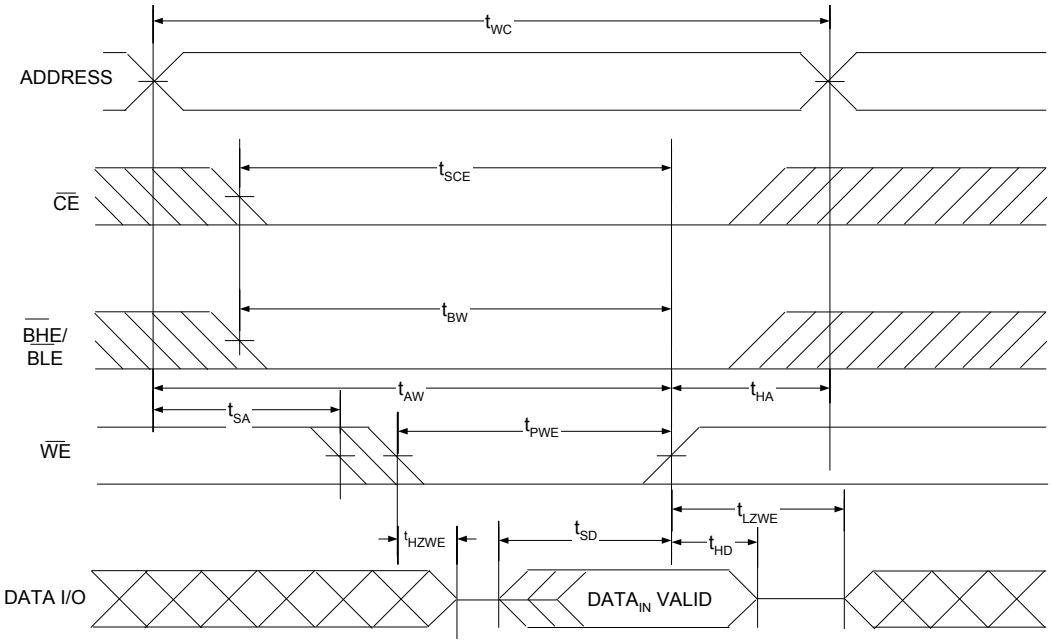


Notes

18. The device is continuously selected. $\overline{OE}$ = V_{IL}, $\overline{CE}$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}.
19. $\overline{WE}$ is HIGH for read cycle.
20. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
21. Address valid prior to or coincident with $\overline{CE}$ LOW transition.

Switching Waveforms (continued)

Figure 6. Write Cycle No. 1 ($\overline{WE}$ Controlled) [22, 23, 24]

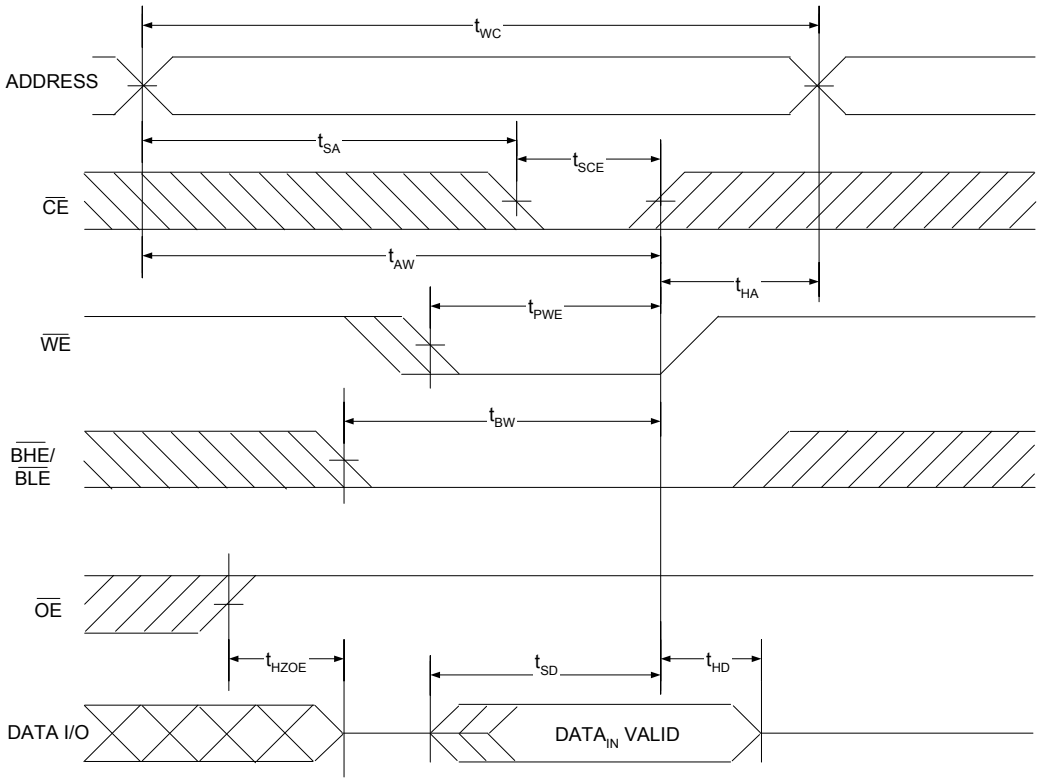


Notes

22. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
23. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE}_1$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
24. Data I/O is in HI-Z state if $\overline{CE}$ = V_{IH}, or $\overline{OE}$ = V_{IH} or $\overline{BHE}$, and/or $\overline{BLE}$ = V_{IH}.

Switching Waveforms (continued)

Figure 7. Write Cycle No. 2 ($\overline{CE}$ Controlled) [25, 26, 27]

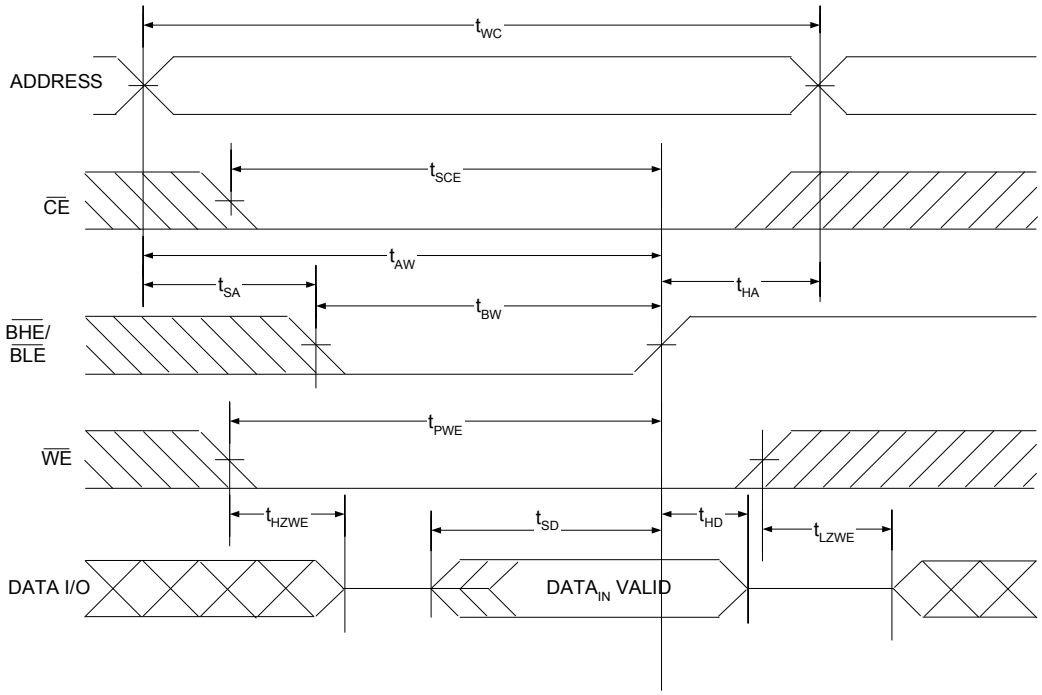


Notes

25. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
26. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE}_1$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
27. Data I/O is in high impedance state if $\overline{CE}$ = V_{IH}, or $\overline{OE}$ = V_{IH} or $\overline{BHE}$, and/or $\overline{BLE}$ = V_{IH}.

Switching Waveforms (continued)

Figure 8. Write Cycle No. 3 ($\overline{BHE}$/$\overline{BLE}$ controlled, $\overline{OE}$ LOW) [28, 29, 30]



Notes

28. For all dual chip enable devices, $\overline{CE}$ is the logical combination of $\overline{CE}_1$ and CE_2. When $\overline{CE}_1$ is LOW and CE_2 is HIGH, $\overline{CE}$ is LOW; when $\overline{CE}_1$ is HIGH or CE_2 is LOW, $\overline{CE}$ is HIGH.
29. The internal write time of the memory is defined by the overlap of $\overline{WE}$ = V_{IL}, $\overline{CE}_1$ = V_{IL}, $\overline{BHE}$ or $\overline{BLE}$ or both = V_{IL}, and CE_2 = V_{IH}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input setup and hold timing must refer to the edge of the signal that terminates the write.
30. Data I/O is in high impedance state if $\overline{CE}$ = V_{IH}, or $\overline{OE}$ = V_{IH} or $\overline{BHE}$, and/or $\overline{BLE}$ = V_{IH}.

Truth Table – CY62157H30-45BVXA

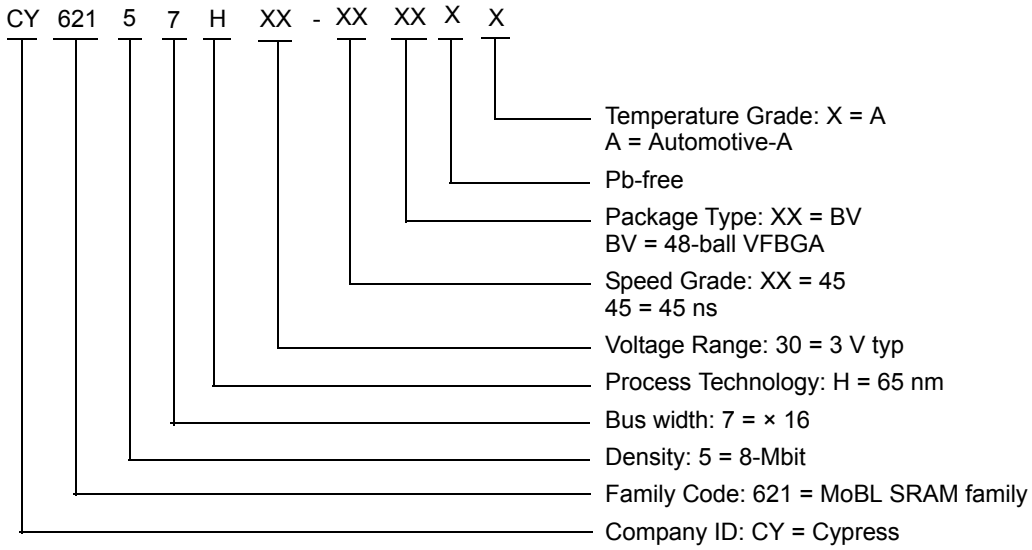
$\overline{CE_1}$	CE_2	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X[31]	X	X	X	X	HI-Z	Deselect/Power-down	Standby (I_{SB})
X[31]	L	X	X	X	X	HI-Z	Deselect/Power-down	Standby (I_{SB})
X[31]	X[31]	X	X	H	H	HI-Z	Deselect/Power-down	Standby (I_{SB})
L	H	H	L	L	L	Data Out (I/O_0–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	H	L	Data Out (I/O_0–I/O_7); HI-Z (I/O_8–I/O_{15})	Read	Active (I_{CC})
L	H	H	L	L	H	HI-Z (I/O_0–I/O_7); Data Out (I/O_8–I/O_{15})	Read	Active (I_{CC})
L	H	H	H	X	X	HI-Z	Output disabled	Active (I_{CC})
L	H	L	X	L	L	Data In (I/O_0–I/O_{15})	Write	Active (I_{CC})
L	H	L	X	H	L	Data In (I/O_0–I/O_7); HI-Z (I/O_8–I/O_{15})	Write	Active (I_{CC})
L	H	L	X	L	H	HI-Z (I/O_0–I/O_7); Data In (I/O_8–I/O_{15})	Write	Active (I_{CC})

Note
31. The ‘X’ (Don’t care) state for the chip enables refer to the logic state (either HIGH or LOW). Intermediate voltage levels on these pins is not permitted.

Ordering Information

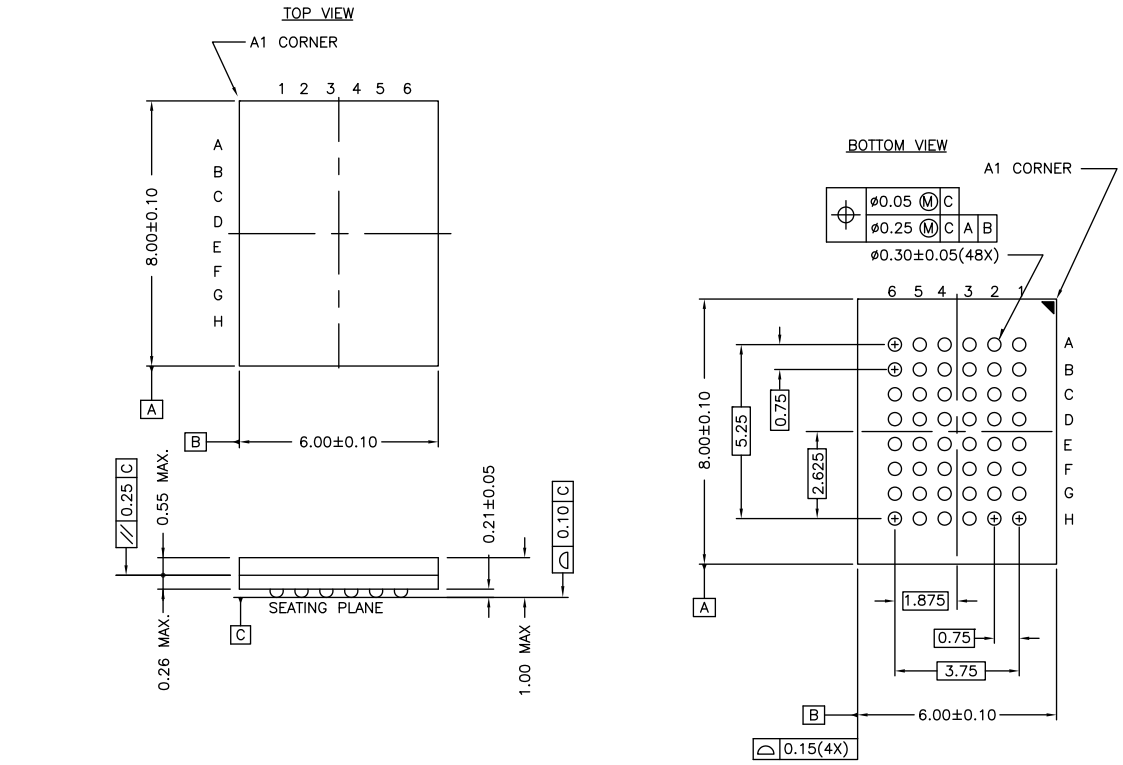
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62157H30-45BVXA	51-85150	48-ball VFBGA (6 × 8 × 1 mm) (Pb-free), Package Code: BZ48	Automotive-A

Ordering Code Definitions



Package Diagram

Figure 9. 48-ball VFBGA (6 × 8 × 1.0 mm) BV48/BZ48 Package Outline, 51-85150



NOTE:
PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress web.

51-85150 *H

Acronyms

Acronym	Description
$\overline{BHE}$	byte high enable
$\overline{BLE}$	byte low enable
$\overline{CE}$	chip enable
CMOS	complementary metal oxide semiconductor
I/O	input/output
$\overline{OE}$	output enable
SRAM	static random access memory
VFBGA	very fine-pitch ball grid array
$\overline{WE}$	write enable

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
µA	microamperes
µs	microseconds
mA	milliamperes
mm	millimeters
ns	nanoseconds
Ω	ohms
%	percent
pF	picofarads
V	volts
W	watts

Document History Page

Document Title: CY62157H30-45BVXA Automotive, 8-Mbit (512K Words × 16-Bit) Static RAM with Error-Correcting Code (ECC) Document Number: 002-19620				
Rev.	**ECN No.**	**Orig. of Change**	**Submission Date**	**Description of Change**
**	5732772	NILE	05/10/2017	New data sheet.
*A	5749424	NILE	05/25/2017	Updated DC Electrical Characteristics: Changed minimum value of V_{OH} parameter from 2.2 V to 2.4 V corresponding to Operating Range “2.7 V to 3.6 V” and Test Condition “V_{CC} = Min, I_{OH} = –1.0 mA”.

Sales, Solutions, and Legal Information

Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at Cypress Locations.

Products

ARM® Cortex® Microcontrollers	cypress.com/arm
Automotive	cypress.com/automotive
Clocks & Buffers	cypress.com/clocks
Interface	cypress.com/interface
Internet of Things	cypress.com/iot
Memory	cypress.com/memory
Microcontrollers	cypress.com/mcu
PSoC	cypress.com/psoc
Power Management ICs	cypress.com/pmic
Touch Sensing	cypress.com/touch
USB Controllers	cypress.com/usb
Wireless Connectivity	cypress.com/wireless

PSoC® Solutions

PSoC 1 | PSoC 3 | PSoC 4 | PSoC 5LP

Cypress Developer Community

Forums | WICED IOT Forums | Projects | Video | Blogs | Training | Components

Technical Support

cypress.com/support